



IS66WVQ4M4DALL/BLL

IS67WVQ4M4DALL/BLL

16Mb QUADRAM
1.8V/3.0V SERIAL PSRAM MEMORY WITH 200MHZ QUAD DDR
(x4 xSPI INTERFACE) PROTOCOL

ADVANCED DATA SHEET

16Mb QUADRAM

SERIAL PSRAM MEMORY WITH 200MHz QUAD DDR (x4 xSPI) Interface

ADVANCED INFORMATION

FEATURES

• Industry Standard Serial Interface

- Quad DDR (x4 xSPI) Interface:
Command (1 byte) =SDR
Address (2-byte) & Data = DDR
- Low Signal Counts :7 Signal pins (CS#, SCLK, DQSM, SIO0~SIO3)

• High Performance

- Double Data Rate (DDR) Operation:
200MHz (200MB/s) at 1.8V VCC ⁽¹⁾
133MHz (133MB/s) at 3.0V VCC
- Source Synchronous Output signal during Read Operation (DQSM)
- Data Mask during Write Operation (DQSM)
- Configurable Latency for Read/Write Operation
- Supports Variable Latency mode and Fixed Latency mode
- Configurable Drive Strength
- Supports Wrapped Burst mode and Continuous mode
- Supports Deep Power Down mode
- Hidden Refresh

• Burst Operation

- Configurable Wrapped Burst Length :
16, 32, 64, and 128
- Continuous Operation:
 - Continues Read operation until the end of array address (No Wrapped)
 - Continues Write operation even after the end of array address (Wrapped to first address)

• Low Power Consumption

- Single 1.7V to 1.95V Voltage Supply
- Single 2.7V to 3.6V Voltage Supply
- TBD mA Active Read Current (TYP.)
- TBD μ A Standby Current (TYP.)
- TBD μ A Deep Power Down (1.8V, TYP.)

• Hardware Features

- **SCLK Input:** Serial clock input
- **SIO0 – SIO3:**
Serial Data Input or Serial Data Output
- **DQSM:**
 - Output during command, address transactions as Refresh Collision Indicator
 - Output during read data transactions as Read Data Strobe
 - Input during write data transactions as Write Data Mask
- **RESET#:** Hardware Reset pin

• Temperature Grades

- Industrial: -40°C to +85°C
- Extended: -40°C to +105°C
- Auto (A3) Grade: -40°C to +125°C

• Industry Standard PACKAGE

- B = 24-ball TFBGA 6x8mm 5x5 Array
- M = 16-pin 300mil SOIC ⁽¹⁾
- KGD (Call Factory)

Note:

1. 133MHz (max.) for 16-pin SOIC package

GENERAL DESCRIPTION

The IS66/67WVQ4M4DALL/BLL are integrated memory device containing 16Mb Pseudo Static Random Access Memory, using a self-refresh DRAM array organized as 2M words by 8 bits.

The device supports Quad DDR interface, which is compatible with JEDEC standard x4 xSPI Flash.

The device supports Very Low Signal Count (7 signal pins; SCLK, CS#, DQSM, and 4 SIOs), Hidden Refresh Operation, and Automotive temperature (A3, -40°C to +125°C) operation.

Due to DDR operation, minimum transferred data size is a byte (8 bits) through 4 SIO pins.

PERFORMANCE SUMMARY

Read / Write Operation		
Package	VCC	Maximum Clock Rate
24-ball BGA	1.8V	200MHz
	3.0V	133MHz
16-pin SOIC	1.8V	133MHz
	3.0V	

Maximum Current Consumption		
Burst Read or Write (Continuous Burst at 200MHz, 1.8V)		75 mA
Power On Reset		35 mA
Standby (CS# = High, 125°C)	3V	TBD uA
	1.8V	TBD uA
Deep Power Down (CS# = High, 125°C)	3V	TBD uA
	1.8V	TBD uA

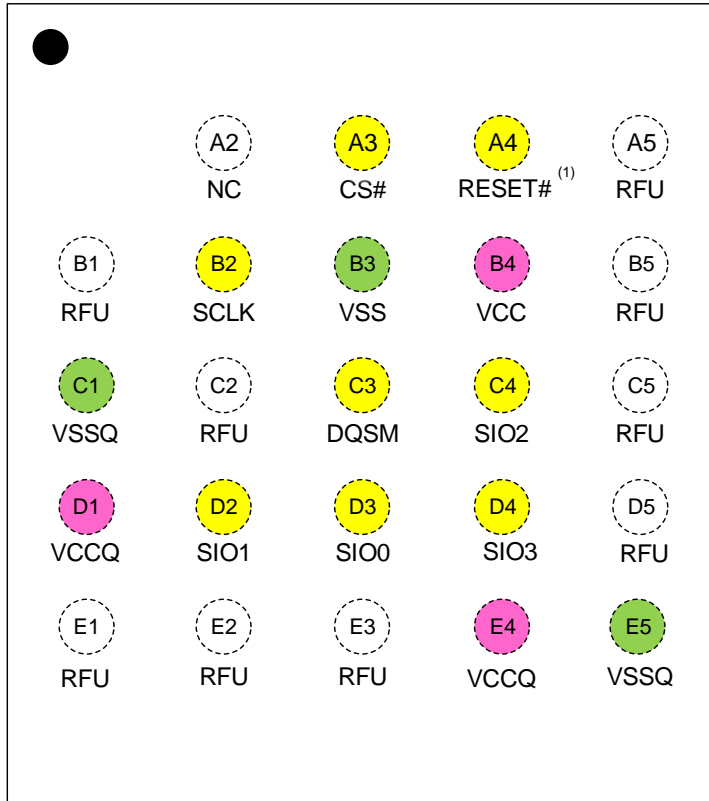
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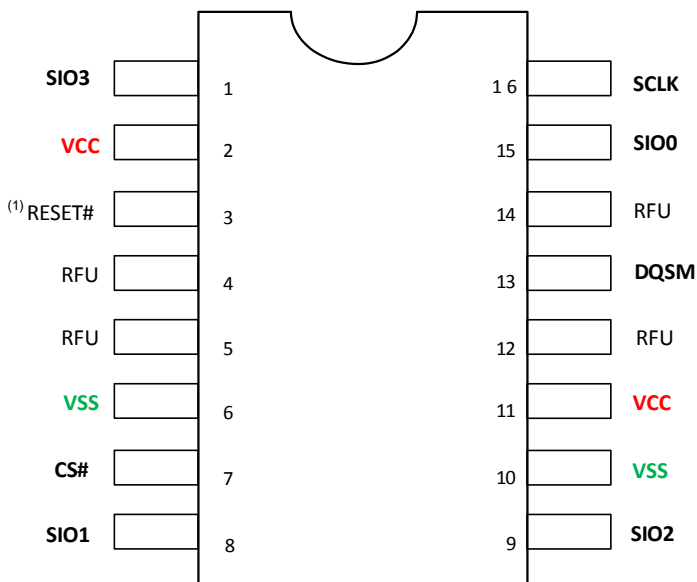
1. PIN CONFIGURATION

24-ball TFBGA (5x5 ball array)

Top View, Balls Facing Down



16-pin SOIC 300mil



Note:

1. RESET# pin can be left floating when not used.

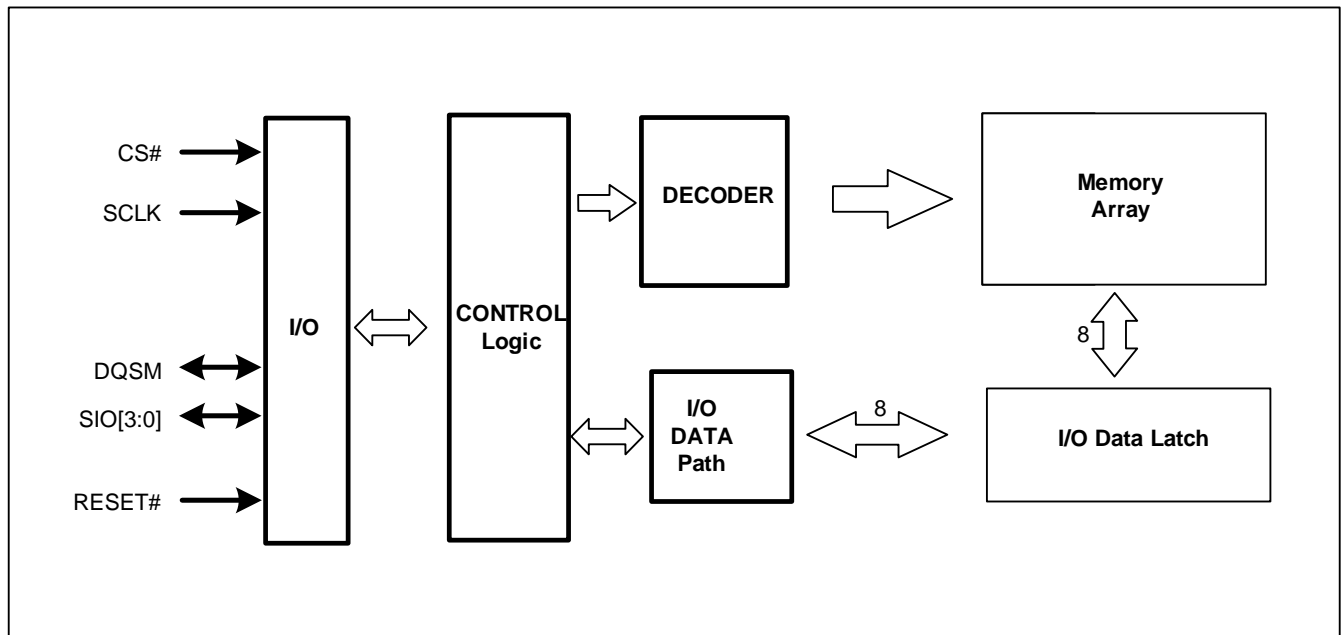
2. PIN DESCRIPTIONS

SYMBOL	TYPE	DESCRIPTION
CS#	INPUT	Chip Select:
DQSM	INPUT/OUTPUT	Refresh Collision Indicator ⁽²⁾, Data Strobe Signal in Read operation, and Write Data Mask in Write operation:
RESET# ⁽¹⁾	INPUT	RESET#: The RESET# pin is a hardware RESET signal. When RESET# is driven High, the memory is in the normal operating mode. When RESET# is driven Low, the memory enters reset mode and output is High-Z.
SIO0-SIO3	INPUT	Serial Data Input & Output pins.
SCLK	INPUT	Serial Data Clock: Synchronized Clock for input and output timing operations.
VCC	POWER	Power Supply
VCCQ	POWER	IO Power Supply
VSS	GROUND	Ground
VSSQ	GROUND	IO Ground
RFU	Reserved	RFU: Reserved for future use: May or may not be connected internally.

Notes:

1. RESET# pin has an internal pull-up.
2. Contact ISSI MKT for DQSM without Refresh Collision Indicator

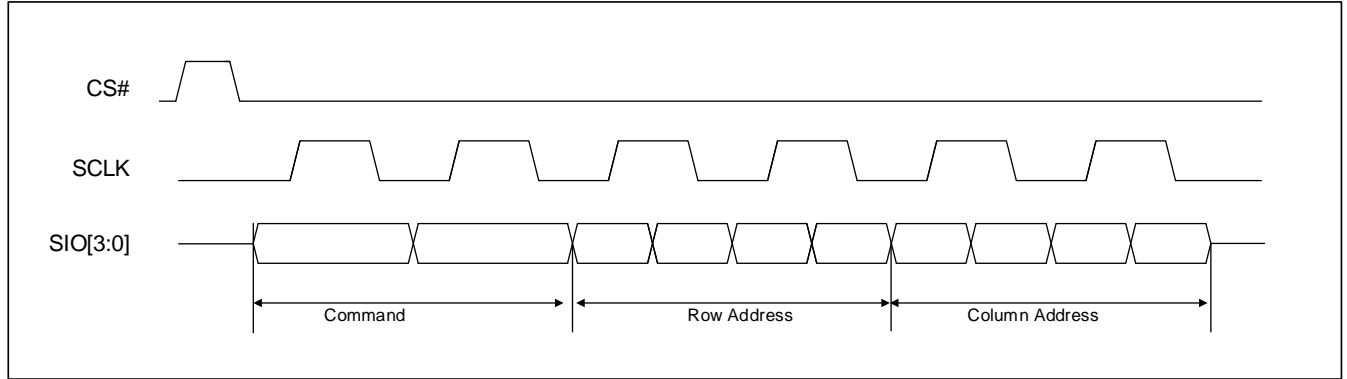
3. BLOCK DIAGRAM



4. COMMAND AND ADDRESS ASSIGNMENTS

The device is serial interface, so all command and address inputs are transferred through SIO pins.

Figure 4.1 Command and Address Cycles



Notes:

1. The figure shows the initial six clock cycles of input operations.
2. Command and Address information is “center aligned” with the clock during both Read and Write operations.

Table 4.1 Command / Address bit assignment

Clock	1 st clock	2 nd clock	3 rd clock	4 th clock	5 th clock	6 th clock				
Function	Command (8-bit)		Row address		Column address					
SIO[3]	Command		Reserved	RA11	RA7	RA3	Reserved	CA6	CA2	Reserved
SIO[2]			Reserved	RA10	RA6	RA2	Reserved	CA5	CA1	Reserved
SIO[1]			Reserved	RA9	RA5	RA1	Reserved	CA4	CA0	Reserved
SIO[0]			RA12	RA8	RA4	RA0	CA7 ⁽³⁾	CA3	Reserved	Reserved

Notes:

1. The 16Mb QUADRAM address assignments:
 - Row Address 12 ~ 0: 8K (13 bits), Column Address 7 ~ 0: 256 (8 bits), 16Mb density = 8K X 256 X 8 (bytes)
2. Data is always transferred in full byte increment (byte granularity -8 bits-transfer).
3. CA7 becomes RFU in 8Mb density.

Table 4.2 Command / Address bit assignment

Command	Clock 1, 2		Clock 3, 4		Clock 5, 6	
	Command (SDR)		Row address (DDR)		Column address (DDR)	
Memory READ with continuous burst	Ah	0h	RA[12:0]		CA[7:0] ⁽¹⁾	
Memory READ with wrapped burst	8h	0h	RA[12:0]		CA[7:0] ⁽¹⁾	
Memory WRITE with continuous burst	2h	0h	RA[12:0]		CA[7:0] ⁽¹⁾	
Memory WRITE with wrapped burst	0h	0h	RA[12:0]		CA[7:0] ⁽¹⁾	
Identification Register (read only)	Ch or Eh	0h	00h	00h	00h	00h
Configuration Register READ	Ch or Eh	0h	00h	04h	00h	00h
Configuration Register WRITE	6h	0h	00h	04h	00h	00h
ECC Register READ	Ch or Eh	0h	00h	04h	00h	03h
ECC Register WRITE	6h	0h	00h	04h	00h	03h
Preamble Bit Pattern READ	Fh	0h	Don't care		CA[7:1] Don't care CA[0] Pattern Selection	

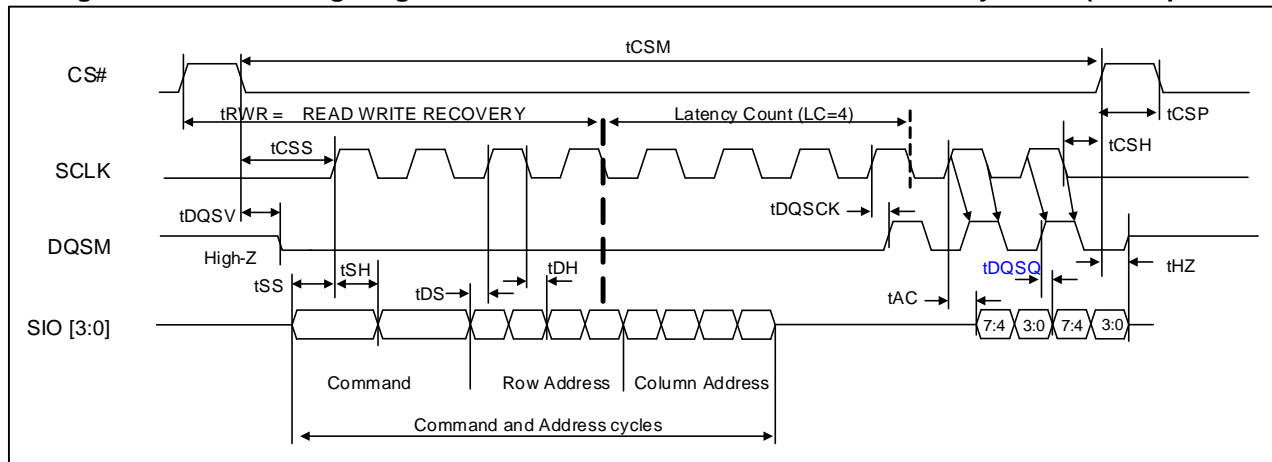
Note:

1. CA[6:0] in 8Mb density:

5. Memory READ/WRITE OPERATIONS

5.1 MEMORY READ OPERATIONS

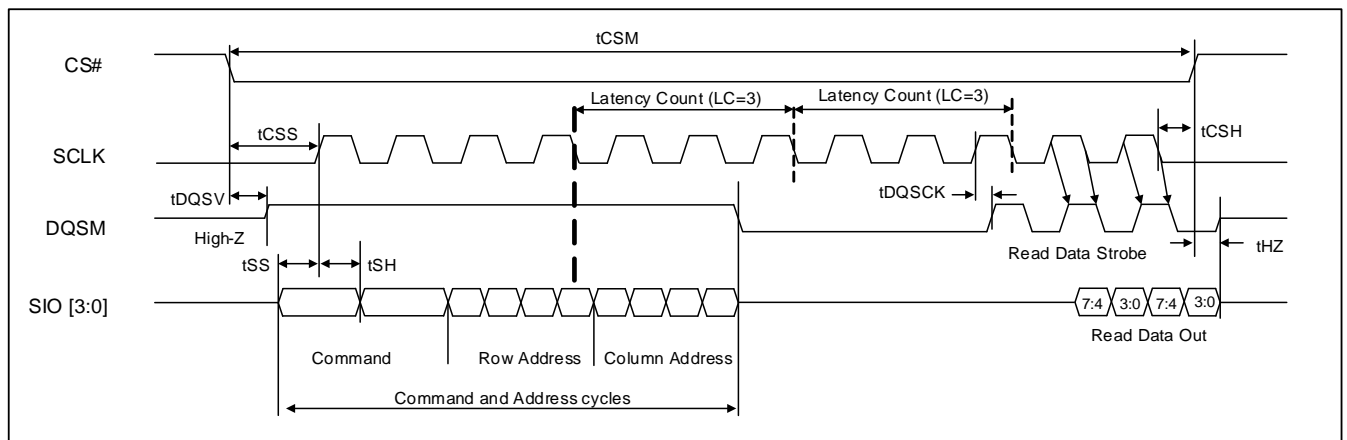
Figure 5.1 Read Timing Diagram - No Refresh Collision at Variable Latency READ (1LC operation)



Notes:

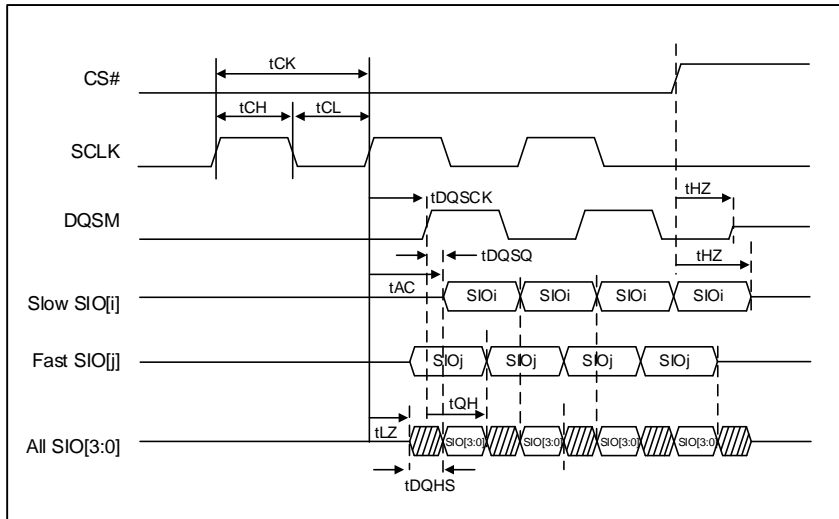
1. The Latency count is defined by the initial latency value in a configuration register.
2. Latency count (LC) is 4 clocks, CR [8] =1 (DQSM 1 clock pre-cycle before Valid READ Data).
3. Diagram in the figure above is representative of **variable latency with no refresh collision access**.
4. Read access (LC) starts once RA [3:0] (falling edge of 4th clock) is captured.
5. The memory drives DQSM during read cycles.
6. DQSM is a read data strobe with data values edge aligned with the transitions of DQSM driven by the device.

Figure 5.2 Read Timing Diagram - Refresh Collision at Variable-Latency READ (2LC operation)

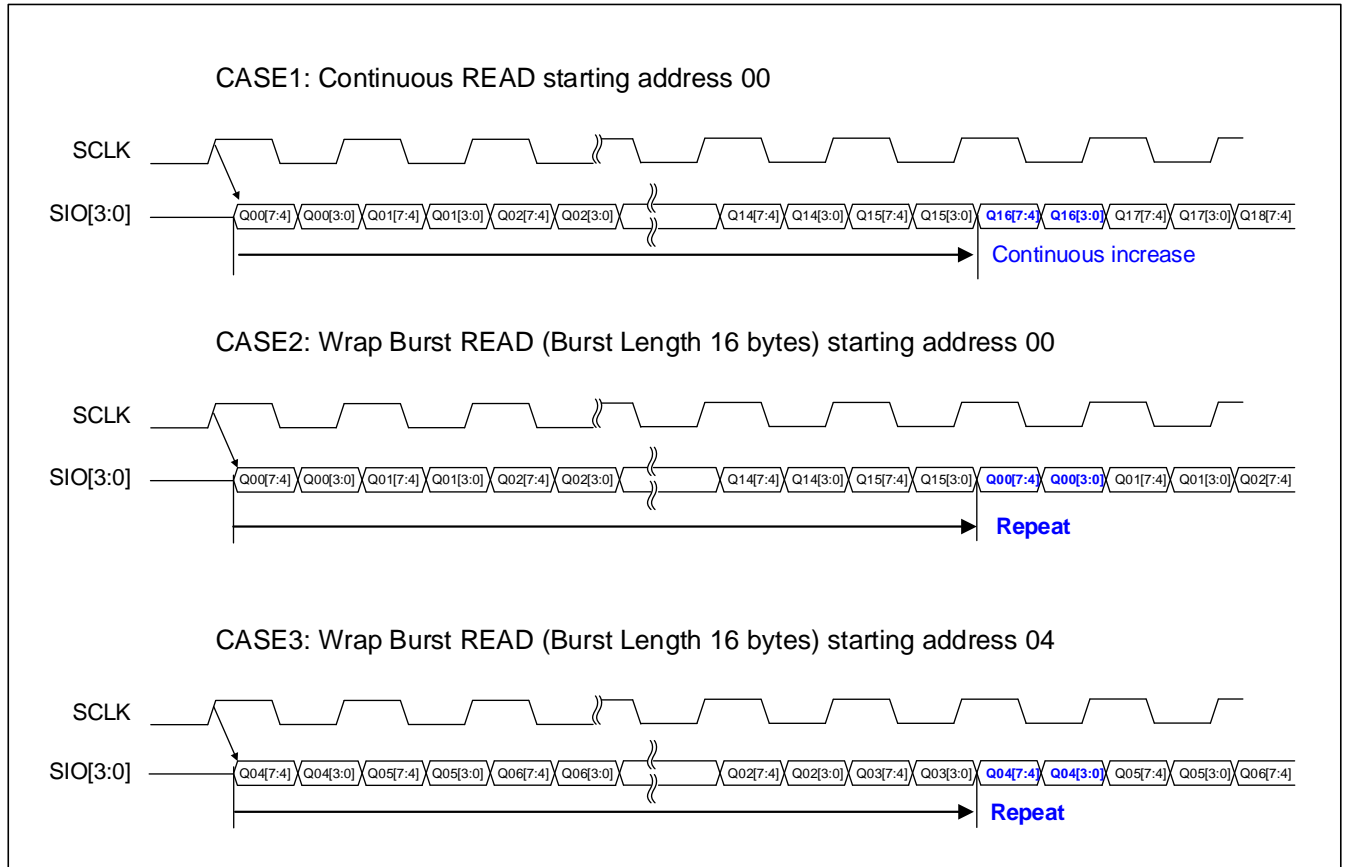


Notes:

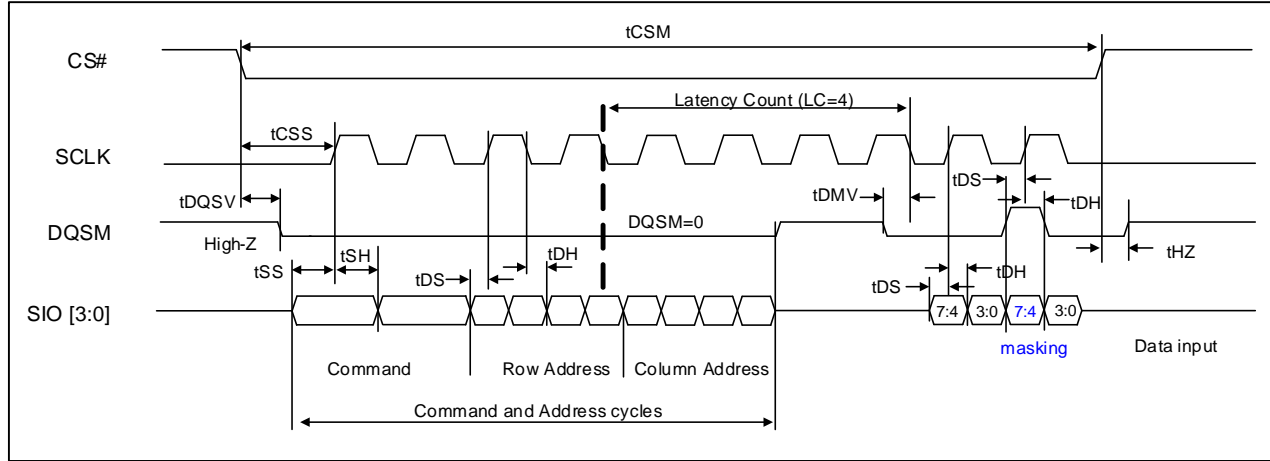
1. The Latency count is defined by the initial latency value in a configuration register.
2. Latency count (LC) is 3 clocks, CR [8] =1 (DQSM 1 clock pre-cycle before Valid READ Data).
3. Diagram in the figure above is representative of **variable latency with refresh collision or fixed-latency access (2LC operation)**.
4. In this Read there is a 2 Latency Count (2LC) for read access.
5. Read access (LC) starts once RA [3:0] is captured.
6. The memory drives DQSM during read cycles.
7. DQSM is a read data strobe with data values edge aligned with the transitions of DQSM driven by the device.
8. **Fixed initial READ access latency outputs the first data at a consistent time regardless of worst-case refresh collisions.**

Figure 5.3 Data Valid Timing

Notes:

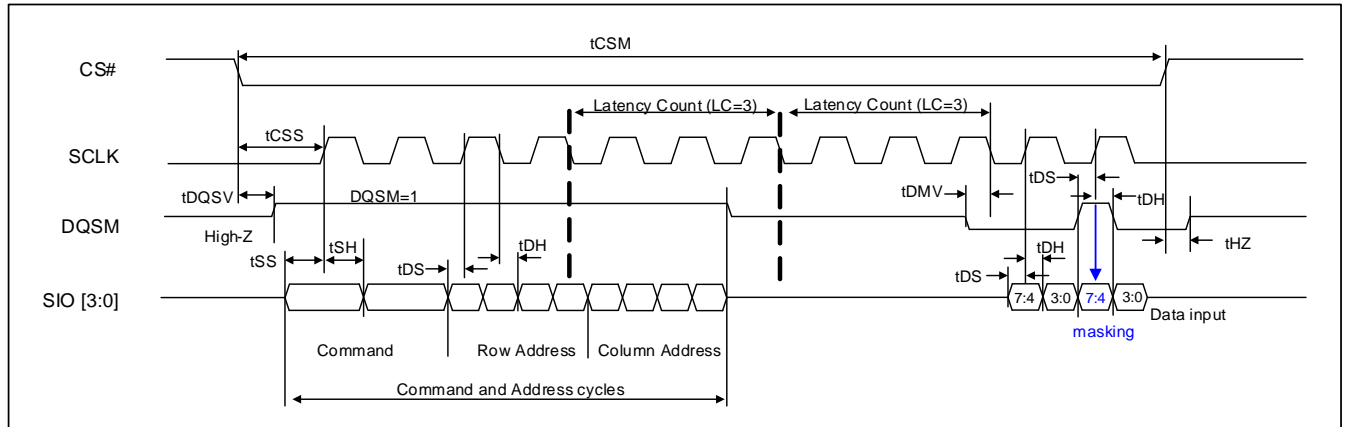
1. Burst READ data valid timing in detail.
2. tAC defines CLK transition to DQ Valid.
3. tDQSK defines CLK transition to DQSM Valid.
4. tDQSQ defines DQSM-DQ skew.
5. tQHS defines Data Hold skew factor.
6. tQH defines DQ hold time from DQSM.

Figure 5.4 READ Burst Wrap

Notes:

1. CS# can stay Low between burst operations, but CS# must not remain Low longer than tCSM.
2. Read operation can be ended at any time by bringing CS# High.
3. Continues Read operation until last address. Continuing beyond last address, undefined data will be available.

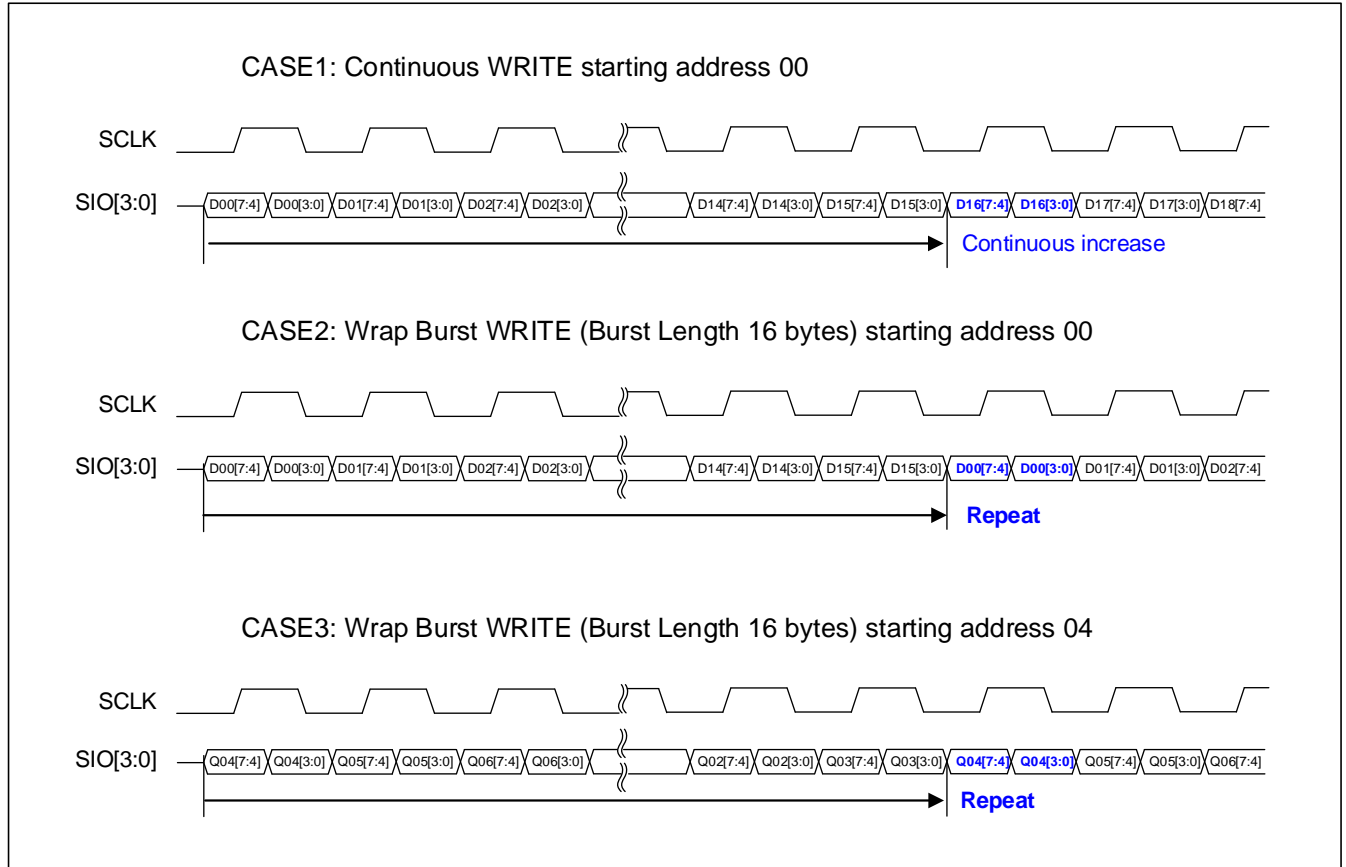
5.2 WRITE OPERATIONS
Figure 5.5 No Refresh Collision at Variable Latency WRITE (1LC) / Data Input Masking

Notes:

1. The Latency count is defined by the initial latency value in a configuration register.
2. Latency count (LC) is 4 clocks.
3. Diagram in the figure above is representative of **variable latency with no refresh collision access**.
4. Write access (LC) starts once RA [3:0] is captured.
5. The memory drives DQSM "Low" during command address cycles and DQSM goes to "Hi-Z" after command address cycles.
6. The system memory controller must drive DQSM to a valid Low before the end of initial latency (t_{DMV}) to provide a data mask preamble time. This can be done during the last cycle of LC cycle.
7. During Write data input, data is center aligned with the clock.
8. During Write data input, DQSM indicates whether each data byte is masked with DQSM High or not masked with DQSM Low.
9. Data inputs [7:4] of second byte are masked.

Figure 5.6 Refresh Collision at Variable Latency WRITE (2LC) / Data Input Masking

Notes:

1. The Latency count is defined by the initial latency value in a configuration register.
2. Latency count (LC) is 3 clocks.
3. Diagram in the figure above is representative of **variable latency with refresh collision or fixed-latency access. (2LC operation)**
4. **In this Write there is a latency count (2LC) for WRITE operation**
5. Write access (LC) starts once RA [3:0] is captured.
6. The memory drives DQSM High during command address cycles and DQSM goes to "Hi-Z" after command address cycles.
7. The system memory controller must drive DQSM to a valid Low before the end of initial latency (t_{DMV}) to provide a data mask preamble time. This can be done during the last cycle of LC cycle.
8. During Write data input, data is center aligned with the clock.
9. During Write data input, DQSM indicates whether each half byte (4-bit) is masked with DQSM High or not masked with DQSM Low.
10. Data inputs [7:4] of second byte are masked.

Figure 5.7 WRITE Burst Wrap



Notes:

1. CS# can stay Low between burst operations, but CS# must not remain Low longer than tCSM.
2. Write operation can be ended at any time by bringing CS# High.
3. When continuous burst write reaches the last address in the memory array, continuing the burst will write to the beginning of the address.

5.3 PREAMBLE BIT DATA PATTERN READ OPERATION

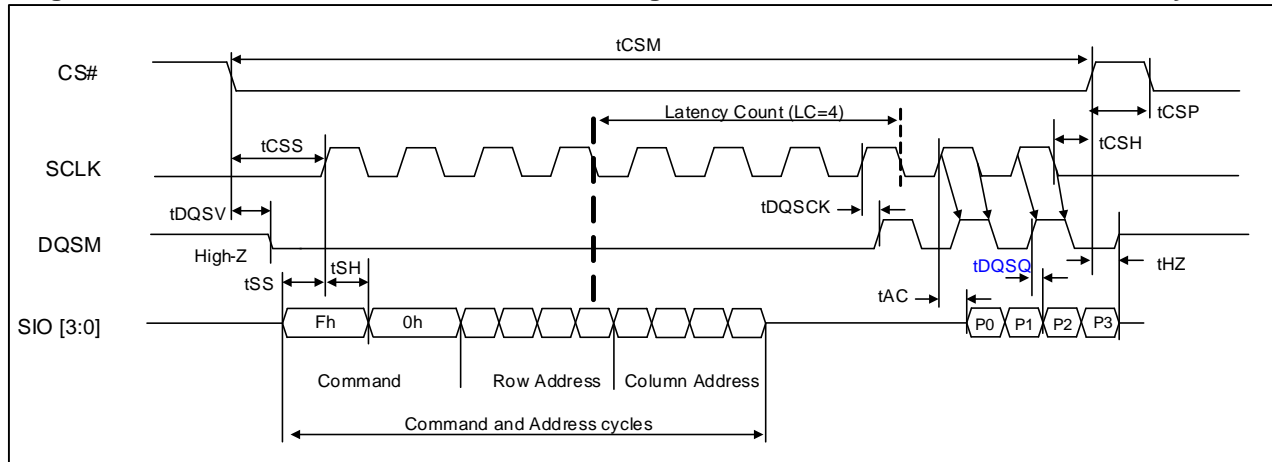
The Preamble Bit Data Pattern READ Operation can improve data capture reliability while the QUADRAM is running in high frequency, while supporting the System/Memory Controller to determine the data output valid windows more easily.

The Preamble Bit is designed as a 16-bits data pattern, it can be output by Preamble Bit READ Command (F0h + 00h). The Row Address and Column Address are “don’t care”, except Column Address CA0 is used for selecting the pattern.

After Preamble Bit READ Command (F0h).and addresses cycles, a fixed 16-bits data pattern will output after initial latency cycles on all 4-SIO pins, according to A0 setting in Column Address. Refer to "[Table 5.1. Preamble Bit Data Pattern SIO assignments](#)".

The Latency Count values are defined in configuration register CR [7-4] which is the same as Read timing diagram.

Figure 5.8 Preamble Bit Data Pattern READ Timing, No Refresh Collision at Variable Latency

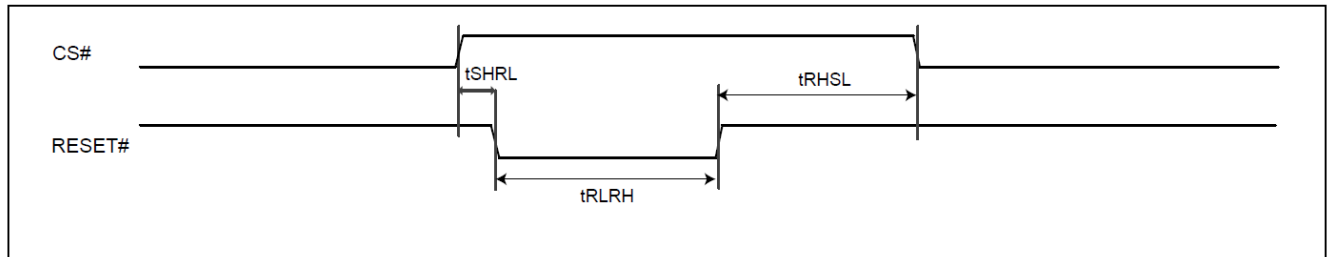


Notes:

1. Latency Count (LC) = 4 clocks, CR[8]=1 (DQSM 1 clock pre-cycle before Valid READ Data)
2. The memory drives DQSM during the entire Data Learning Pattern Read.
3. The required latency count is device and clock frequency dependent.
4. Column address A0 is used for pattern selection, and Row address RA [12:0] and Column address CA [7:1] are don't care.

Table 5.1 Preamble Bit Data Pattern SIO assignments

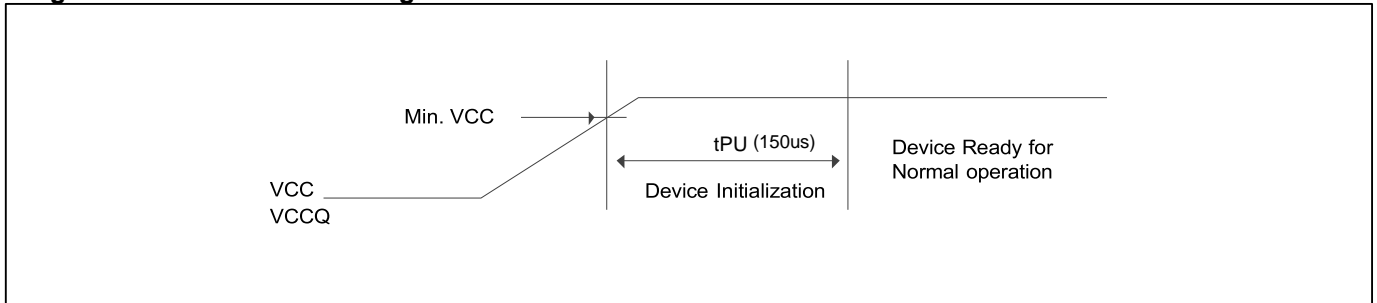
Column Address A0	All SIOs (except SIO3)	SIO3
A0=0	0011 0100 1001 1010	0011 0101 0001 0100
A0=1	0101 0101 0101 0101	0101 0101 0101 0101

5.4 RESET OPERATION
Figure 5.9 RESET Timing

Table 5.2 RESET Timing Parameters

Parameter	Description	Min	Max	Unit
t_{SHRL}	RESET# Low after CS# High	15	-	ns
t_{RLRH}	RESET# Low Pulse width	10	-	us
t_{RHSL}	RESET# High before CS# Low	10	-	us

5.5 POWER-UP INITIALIZATION

Figure 5.10 POWER-UP Timing

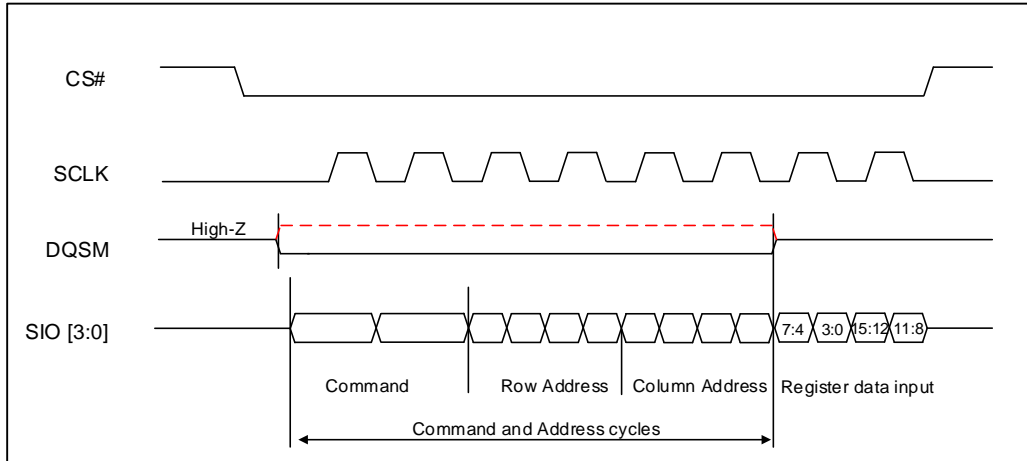


6. REGISTER

The device has 16 bit Configuration Register and ID Register, and they can be accessed by Register Read or Write command.

6.1 REGISTER READ/WRITE OPERATION

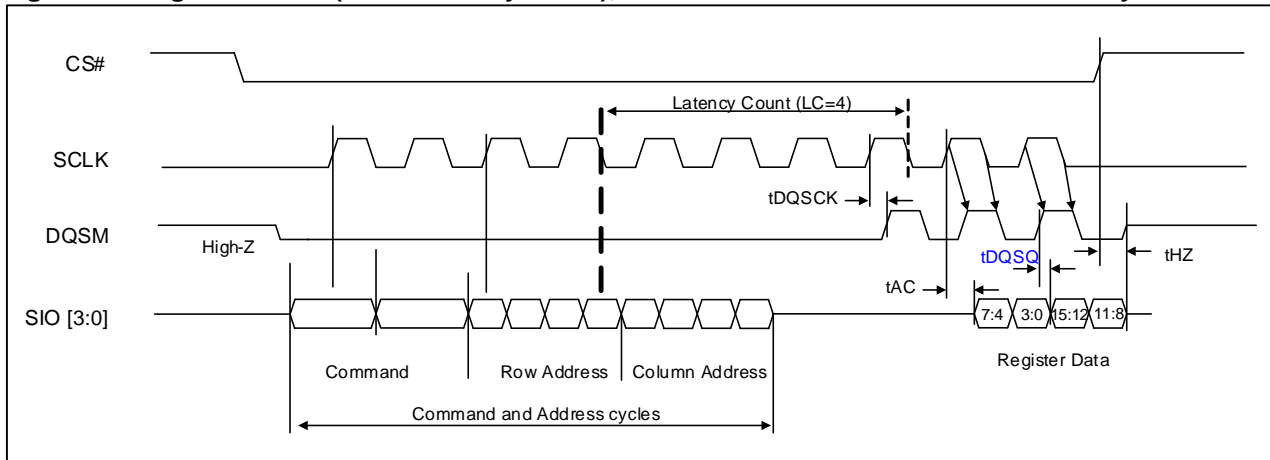
Figure 6.1 Register WRITE



Notes:

1. The device drives DQSM “Low or High for Refresh indication” during command address cycles, which must be ignored by host. DQSM goes to “Hi-Z” after command address cycles.
2. The register value is always provided immediately after the Command Address cycles (0 cycle latency)
3. The DQSM signal keep Hi-Z during register data-input cycles. DQSM will be ignored by host during entire register write operation.
4. **Least Significant Byte first ([7:0]), and Most Significant Byte ([15:8]) later.**

Figure 6.2 Register READ (Initial Latency = 1LC), No Refresh Collision at Variable Latency



Notes:

1. The Latency count is defined by the initial latency value in a configuration register.
2. Latency count (LC) is 4 clocks, CR [8] =1 (DQSM 1 clock pre-cycle before Valid READ Data).
3. Diagram in the figure above is representative of **variable latency with no refresh collision access**.
4. Read access (LC) starts once RA [3:0] is captured (falling edge of 4th Row address clock)
5. The memory drives DQSM during read cycles.
6. DQSM is a read data strobe with data values edge aligned with the transitions of DQSM driven by the device.

6.2 CONFIGURATION REGISTER

The Configuration Register is able to change the defaulted status of the device. The device will be configured after the CR bit is set.

Table 6.1 Configuration Register

	Bit	Function	Settings (Binary)
Most Significant Byte	15	Deep Power Down Enable	1- Normal operation (default) 0- Writing 0 to CR [15] causes the device to enter Deep Power Down.
	14-12	ODS (Output Drive Strength)	Refer to " Table 6.2. Output Driver Strength Table "
	11-9	Reserved	Set to 000b
	8	DQSM READ Pre-cycle	1 - 1 clock 0 - 0 clock (default)
Least Significant Byte	7-4	Latency counter	Refer to " Table 6.3. Latency counter Table "
	3	Initial Access Latency	0 - Variable Latency (default) 1 - Fixed Latency
	2	Reserved	Set to 0b
	1-0	Burst Length	00- 128 bytes 01- 64 bytes 10- 32 bytes (default) 11- 16 bytes

Table 6.2 Output Driver Strength Table

CR[14]	CR[13]	CR[12]	Description
0	0	0	146 Ohms
0	0	1	76 Ohms
0	1	0	52 Ohms
0	1	1	41 Ohms
1	0	0	34 Ohms
1	0	1	30 Ohms
1	1	0	26 Ohms
1	1	1	24 Ohms (Default)

Table 6.3 Latency counter Table

CR[7:4]	Latency Counter
0000	3 clocks
0001	4 clocks
0010	5 clocks(default at 3V)
0011	6 clocks
0100	7 clocks
0101	8 clocks(default at 1.8V)
0110~1111	Reserved

6.2.1 WRAPPED BURST LENGTH
Table 6.4 Wrapped Burst Sequences

Command	Configuration Register[1:0]	Burst Type	Wrap Boundary Col. Addr	Start address (Hex)	Address Sequence (Hex):Bytes
Read	00	Wrap 128	CA[6:0]	XXXXXX06	06, 07, 08, 09, 7E, 7F , 00, 01, 02, 03, 04, 05, 06, 07,
Write	00	Wrap 128	CA[6:0]	XXXXXX06	06, 07, 08, 09, 7E, 7F , 00, 01, 02, 03, 04, 05, 06, 07,
Read	01	Wrap 64	CA[5:0]	XXXXXX02	02, 03, 04, 05, 3E, 3F , 00, 01, 02, 03, 04, 05, 06, 07,
Write	01	Wrap 64	CA[5:0]	XXXXXX02	02, 03, 04, 05, 3E, 3F , 00, 01, 02, 03, 04, 05, 06, 07,
Read	10	Wrap 32	CA[4:0]	XXXXXX1A	1A, 1B, 1C, 1D, 1E, 1F , 00, 01, 0E, 0F, 10, 11, 12,
Write	10	Wrap 32	CA[4:0]	XXXXXX1A	1A, 1B, 1C, 1D, 1E, 1F , 00, 01, 0E, 0F, 10, 11, 12,
Read	11	Wrap 16	CA[3:0]	XXXXXX0A	0A, 0B, 0C, 0D, 0E, 0F , 00, 01, 08, 09, 0A, 0B, 0C,
Write	11	Wrap 16	CA[3:0]	XXXXXX0A	0A, 0B, 0C, 0D, 0E, 0F , 00, 01, 08, 09, 0A, 0B, 0C,
Read	XX	Continuous	X	XXXXXX0C	0C, 0D, 0E, 0F, 10, 11, 12, 13, 14, 15, 16, 17,
Write	XX	Continuous	X	XXXXXX0C	0C, 0D, 0E, 0F, 10, 11, 12, 13, 14, 15, 16, 17,

Notes: When Continuous burst type is operated on burst operations, Memory access address will increase continuously regardless of Burst Wrap Length code.

6.2.2 INITIAL LATENCY (CR [3])

Initial Latency for Variable Latency setting (CR [3]=0) is LC or 2LC , based on Refresh Collision like below table. So host chipset must monitor DQSM signal, which indicates Refresh Collision occurrence or not. But Initial Latency for Fixed Latency setting (CR [3] = 1) is always 2LC.

Table 6.5 Variable Latency (CR[3] = 0)

Latency code CR[7:4]	Initial Latency Counter		Maximum Operating Frequency (Mhz)
	No Refresh Collision (LC)	Refresh Collision (2LC)	
0000	3 clocks	6 clocks	83Mhz
0001	4 clocks	8 clocks	100Mhz
0010	5 clocks(default at 3V)	10 clocks	133Mhz
0011	6 clocks	12 clocks	150MHz
0100	7 clocks	14 clocks	-
0101	8 clocks(default at 1.8V)	16 clocks	200Mhz
0110 - 1111	Reserved	Reserved	NA

Notes: Default setting for 1.8V device is “0101”, and that for 3.0V device is “0010”.

Table 6.6 Initial Latency Summary Table⁽¹⁾

Destination	Operating mode	Variable mode (default) initial Latency Count		Fixed mode Initial Latency Count
		No Refresh Collision	Refresh Collision	
Memory	READ	1LC	2LC	2LC
	WRITE	1LC	2LC⁽²⁾	2LC⁽²⁾
Register	READ	1LC	2LC⁽²⁾	2LC⁽²⁾
	WRITE	0LC		0LC

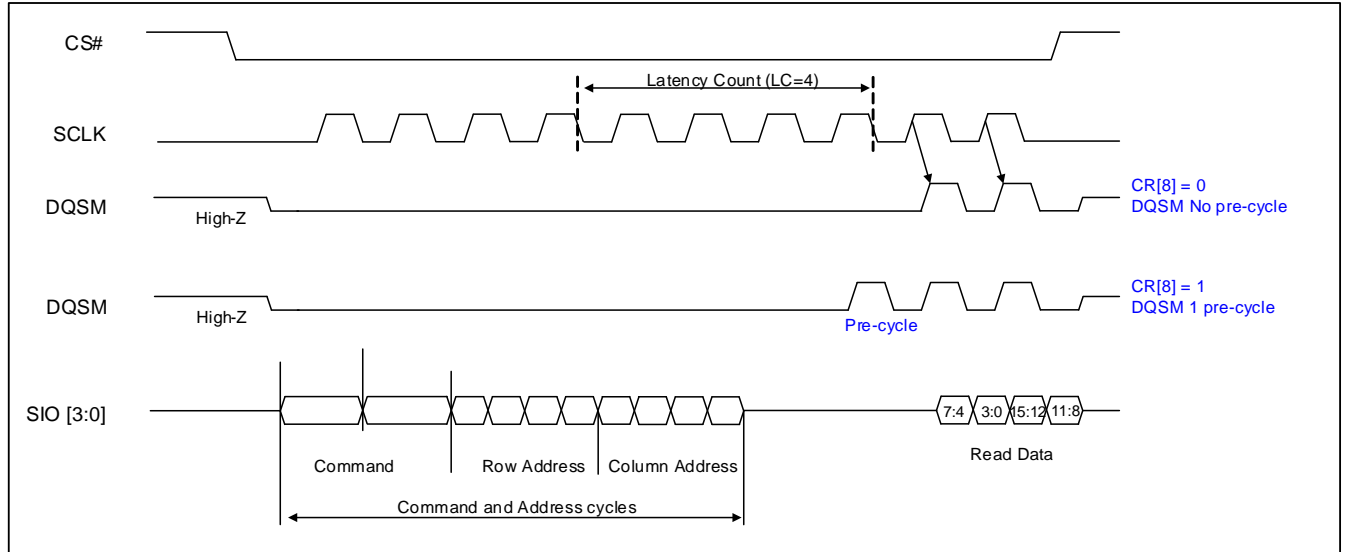
Notes:

1. LC means Latency Counter clocks, which is in Configuration Register Bit [7:4], as defined in "Table 6.1" and "Table 6.3".
2. Contact ISSI MKT if 1LC is required instead of 2LC.

6.2.3 DQSM READ Pre-Cycle (CR [8])

CR [8] defines DQSM Pre-Cycle.

Figure 6.3 DQSM pre-cycle Timing, No Refresh Collision at Variable Latency READ (1LC operation)



Notes:

1. Latency count (LC) is 4 clocks.
2. When Configuration Register bit [8] = 0, the Device will output DQSM with valid data cycle.
3. When Configuration Register bit [8] = 1, the Device will output 1 pre-cycle (dummy DQSM) prior to valid data cycle.
4. The memory drives DQSM during read cycles.

6.2.4 Deep Power Down (CR [15])

CR [15] defines DQSM Pre-Cycle.

Figure 6.4 Deep Power Down Entry Timing

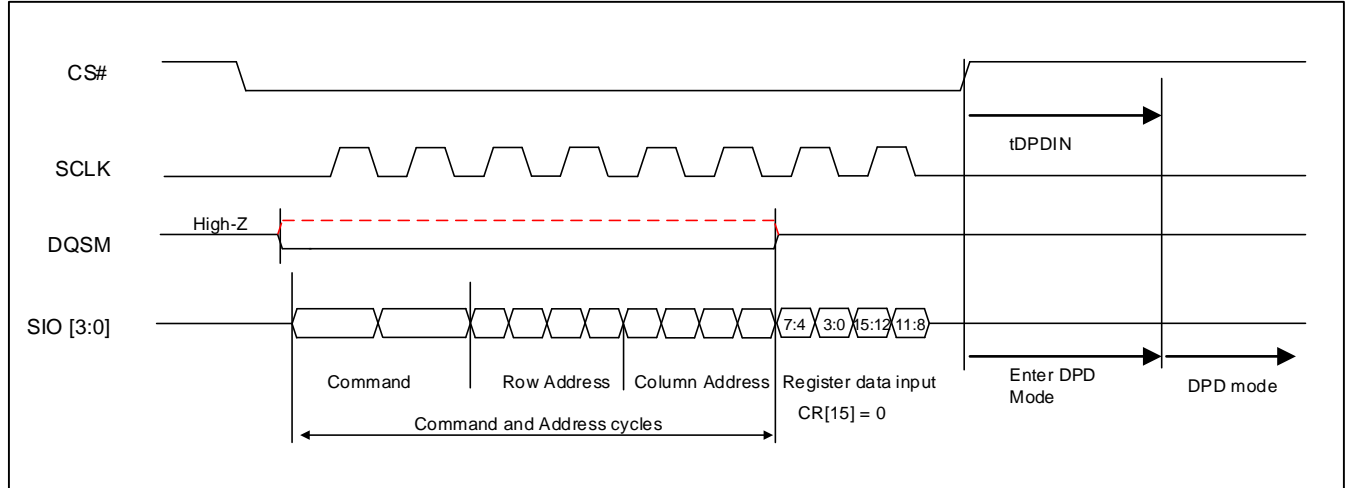
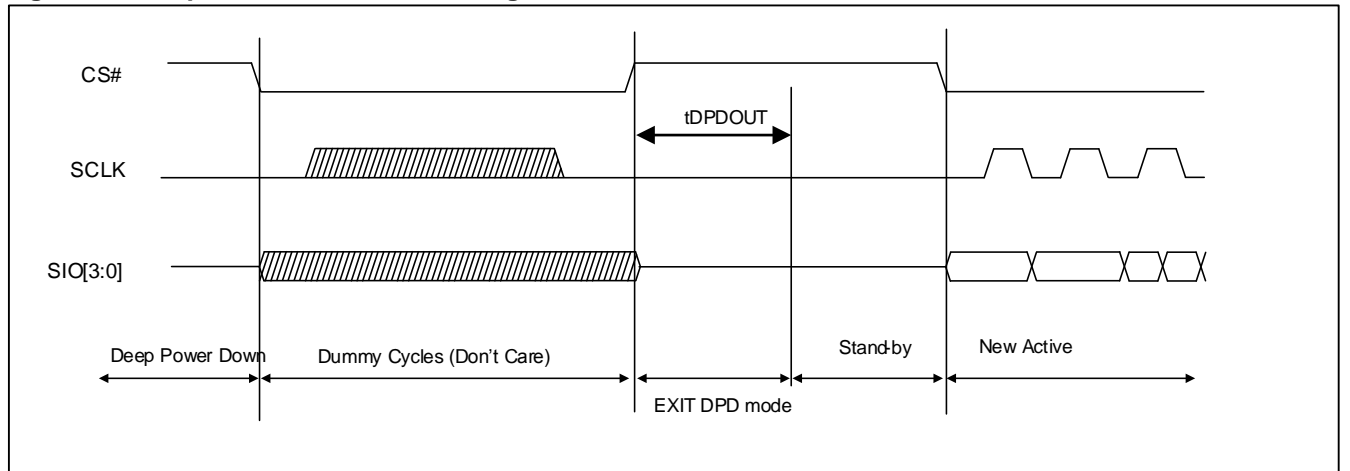


Figure 6.4 Deep Power Down Exit Timing



Note: Memory Cell Data cannot be retained at deep power down(DPD) mode.

Table 6.7 Deep Power Down Timing Parameters

Parameter	Description	Min	Max	Unit
tDPDIN	Deep Power Down CR[15]=0 register write to DPD power level	150	-	us
tDPDX	CS# Low period to exit from Deep Power Down	200	-	ns
tDPDOUT	CS# Low then High to Standby wakeup time	-	150	us

6.3 DEVICE IDENTIFICATION REGISTER

It is a read only, non-volatile, word register that provides device information. The device information fields can be identified as below.

- a. Device Type
- b. Density
 - i. Row address bit count
 - ii. Column address bit count
- c. Manufacturer

Table 6.8 ID Register

Bits	Function	Settings (Binary)
15 - 13	Device Voltage	000: 1.8V 001: 3V
12 - 8	Row address bit count	00000 : 1 row address 01100 : 13 row address 11111 : 32 row address
7 - 4	Column address bit count	0000 : 1 column address 0111: 8 column address 1111 : 16 column address
3 - 0	Manufacturer	0011 (ISSI)

6.4 IN BAND RESET

The device offers an additional feature of In-Band RESET function, which uses existing SPI signals to initiate a hardware reset, which is different from existing software reset/hardware reset (dedicated RESET# pin);

- Existing software reset commands often depend on the Flash being in a particular mode before they are effective. This makes software based reset sequences depend on slave device and mode.
- Dedicated RESET# pin requires additional pin over traditional 8-pins of SPI device. Also it requires 1 more signal for reset operation.

In Band-RESET operation requires 2-signal pins; CE# and SIO0.

- CS# is driven active low to select the SPI slave (note1)
- Clock (SCLK) remains stable in either a high or low state(note 2)
- SIO0 is driven low by the bus master, simultaneously with CS# going active low.....(note 3)
- CS# is driven inactive ... (note 4)
- Repeat the above 4 steps, each time alternating the state of SIO0.
- After the fourth CS# pulse, the slave triggers its internal reset.....(note 5)

Note 1 This powers up the SPI slave

Note 2 This prevents any confusion with a command, as no command bits are transferred (clocked)

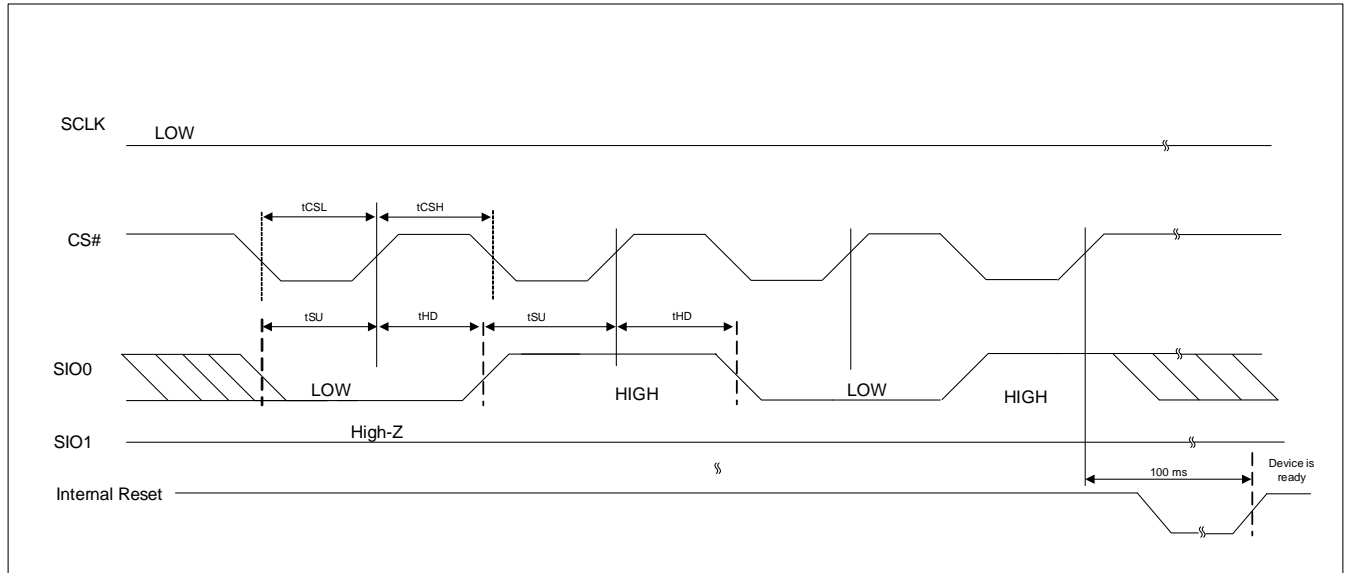
Note 3 No SPI bus slave drives SIO0 during CS# low before a transition of clock. Slave streaming output active is not allowed until after the first edge of clock.

Note 4 The slave captures the state of SIO0 on the rising edge of CS#

Note 5 SIO0 is low on the first CS#, high on the second, low on the third, high on the fourth ... (This provides a 5th, unlike random noise)

NOTE:

This reset sequence is not intended to be used at normal power on, but to be used only when the device is not responding to the system. This reset sequence will be operational from any state that the device may be in. During the reset process, the device will ignore any chip select (command).

Figure 6.5 Timing for In-Band RESET Operation


Parameter	Symbol	Min	Max	Units
CS# Low Pulse	t_{CSL}	500	--	ns
CS# High Pulse	t_{CSH}	500	--	ns
Setup Time	t_{SU}	5	--	ns
Hold Time	t_{HD}	5	--	ns

7. ELECTRICAL CHARACTERISTICS

7.1 ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

Storage Temperature	-65°C to +150°C
Input Voltage with Respect to Ground on All Pins	-0.5V to V _{CC} + 0.5V
All Output Voltage with Respect to Ground	-0.5V to V _{CC} + 0.5V
V _{CC}	-0.5V to +2.5V
Electrostatic Discharge Voltage (Human Body Model) ⁽²⁾	-2000V to +2000V

Notes:

1. Applied conditions greater than those listed in “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. ANSI/ESDA/JEDEC JS-001

7.2 OPERATING RANGE

Operating Temperature	Industrial Grade	-40°C to 85°C
	Extended Grade	-40°C to 105°C
	Automotive Grade A3	-40°C to 125°C
V _{CC} Power Supply	IS66/67WVQ4M4DALL	1.70V (V _{MIN}) –1.95V (V _{MAX}); 1.8V (Typ)
	IS66/67WVQ4M4DBLL	2.7V (V _{MIN}) –3.6V (V _{MAX}); 3.0V (Typ)

7.3 DC CHARACTERISTICS

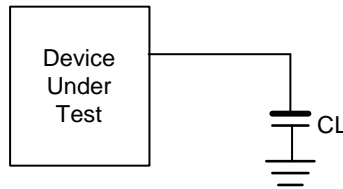
8	Symb	Parameter	Min.	Typ.	Max.	Units	Test Conditions
	I _{LI}	Input Leakage Current 3V Device Reset Signal Only	-	-	±10.0	uA	V _{IN} = V _{SS} to V _{CC} , V _{CC} = V _{CC} max
	I _{LI}	Input Leakage Current 1.8V Device Reset Signal Only	-	-	±5.0	uA	V _{IN} = V _{SS} to V _{CC} , V _{CC} = V _{CC} max
	I _{CC1}	VCC Active Read Current	-	-	75	mA	CS# = V _{IL} , @200MHz, V _{CC} = 1.9V
			-	-	60		CS# = V _{IL} , @166MHz, V _{CC} = 1.9V
			-	-	35		CS# = V _{IL} , @133MHz, V _{CC} = 3.6V
	I _{CC2}	VCC Active Write Current	-	-	75	mA	CS# = V _{IL} , @200MHz, V _{CC} = 1.9V
			-	-	60		CS# = V _{IL} , @166MHz, V _{CC} = 1.9V
			-	-	35		CS# = V _{IL} , @133MHz, V _{CC} = 3.6V
	I _{CC4I}	VCC Standby Current at -40°C to +85°C	-	TBD	200	uA	CS#, V _{CC} =V _{CC} max
	I _{CC4IP}	VCC Standby Current at -40°C to +105°C	-	TBD	300		
	I _{CC4E}	VCC Standby Current at -40°C to +125°C	-	TBD	TBD		
	I _{CC5}	Reset Current	-	TBD	20	mA	CS# = V _{IH} , RESET# = V _{SS} +/- 0.3V, V _{CC} = V _{CC} max
	I _{CC6I}	Active Clock Stop Current at -40°C to +85°C	-	TBD	8	mA	CS# = V _{IL} , RESET# = V _{CC} +/- 0.3V, V _{CC} = V _{CC} max
	I _{CC6IP}	Active Clock Stop Current at -40°C to +105°C	-	TBD	12		
	I _{CC6E}	Active Clock Stop Current at -40°C to +125°C	-	TBD	TBD		
	I _{CC7}	VCC Current during power up	-	-	35	mA	CS#, = H, V _{CC} = V _{CC} max, V _{CC} =V _{CCQ} = 1.95V or 3.6V
	I _{DPD}	Deep Power Down Current 3V	-	-	20	uA	CS#, V _{CC} = 3.6V
	I _{DPD}	Deep Power Down Current 1.8V	-	-	10		CS#, V _{CC} = 1.9V
	V _{IL} ⁽¹⁾	Input Low Voltage	-0.5		0.3V _{CC}	V	
	V _{IH} ⁽¹⁾	Input High Voltage	0.7V _{CC}		V _{CC} + 0.3	V	
	V _{OL}	Output Low Voltage			0.2	V	I _{OL} = 100 μA
	V _{OH}	Output High Voltage	V _{CC} - 0.2			V	I _{OH} = -100 μA

Notes:

- Maximum DC voltage on input or I/O pins is V_{CC} + 0.5V. During voltage transitions, input or I/O pins may overshoot V_{CC} by +2.0V for a period of time not to exceed 20ns. Minimum DC voltage on input or I/O pins is -0.5V. During voltage transitions, input or I/O pins may undershoot GND by -2.0V for a period of time not to exceed 20ns.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC} (Typ), T_A=25°C.

AC Measurement Conditions

Symbol	Parameter	Min	Max	Units
CL	Output Load Capacitance		20	pF
TR,TF	Input Rise and Fall Times	2		V/ns
VIN	Input Pulse Voltages	0V to V _{CCQ}		V
VREFI	Input Timing Reference Voltages	V _{CCQ} /2		V
VREFO	Output Timing Reference Voltages	V _{CCQ} /2		V

Figure 7.1 Test Setup

8.1 PIN CAPACITANCE (TA = 25°C, VCC=1.8V/ 3V, 1MHZ)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
C _{IN}	Input Capacitance (CS#, SCLK)	V _{IN} = 0V	3	-	4.5	pF
C _{IN/OUT}	Input/Output Capacitance (SIO, DQSM)	V _{IN/OUT} = 0V	3	-	4.0	pF

Note:

1. These parameters are characterized and not 100% tested.

8.2 AC CHARACTERISTICS
8.2.1 Read Timing Parameters (1.8V)

Symbol	Parameter	200MHz		166MHz		Unit
		Min.	Max.	Min.	Max.	
tRWR	Read-Write Recovery Time	45	-	54	-	ns
tCK	Clock(CLK) Period	5	-	6	-	ns
tCH	Clock High level width	0.45	-	0.45	-	tCKmi
tCL	Clock Low level width	0.45	-	0.45	-	tCKmi
tHP	Clock half period	Min(tCH,tCL)	-	Min(tCH,tCL)	-	ns
tDQSV	CS# Active to DQSM valid	-	12	-	12	ns
tAC	Clock transition to DQ valid	0.9	5	1	5.5	ns
tDQSCK	Clock transition to DQSM valid	0.9	5	1	5.5	ns
tCSP	CS# High Between READ/WRITE	6	-	6	-	ns
tCSS	CS# Setup to next CLK Rising Edge	3	-	3	-	ns
tCSH	CS# Hold After CLK Falling Edge	2	-	2	-	ns
tSS	SDR Input Setup	0.6	-	0.9	-	ns
tSH	SDR Input Hold	0.6	-	0.9	-	ns
tDS	DDR Input Setup	0.4	-	0.6	-	ns
tDH	DDR Input Hold	0.4	-	0.6	-	ns
tDQSQ	DQSM-DQ Skew	-	0.4	-	0.45	ns
tQHS	Data Hold Skew factor	-	0.8	-	0.85	ns
tQH	DQ hold time from DQSM	tHP-tQHS	-	tHP-tQHS	-	ns
tLZ	Clock to DQ Low-Z	0	-	0	-	ns
tHZ	CS# Inactive to DQSM and DQ High-Z	-	5	-	6	ns
tCSM	Chip Select Maximum	~ 85°C	-	4	-	us
	Low Time	85+°C ~ 125°C	-	1	-	us

8.2.2 Read Timing Parameters (3.0V)

Symbol	Parameter	133Mhz		100Mhz		Unit
		Min.	Max.	Min.	Max.	
tRWR	Read-Write Recovery Time	45	-	50	-	ns
tCK	Clock(CLK) Period	7.5	-	10	-	ns
tCH	Clock High level width	0.45	-	0.45	-	tCKmi
tCL	Clock Low level width	0.45	-	0.45	-	tCKmi
tHP	Clock half period	Min(tCH,tCL)	-	Min(tCH,tCL)	-	ns
tDQSV	CS# Active to DQSM valid	-	12	-	12	ns
tAC	Clock transition to DQ valid	2	7	2	7	ns
tDQSCK	Clock transition to DQSM valid	2	7	2	7	ns
tCSP	CS# High Between READ/WRITE	7.5	-	10	-	ns
tCSS	CS# Setup to next CLK Rising Edge	3	-	3	-	ns
tCSH	CS# Hold After CLK Falling Edge	2	-	2	-	ns
tSS	SDR Input Setup	1.2	-	1.5	-	ns
tSH	SDR Input Hold	1.2	-	1.5	-	ns
tDS	DDR Input Setup	0.8	-	1.0	-	ns
tDH	DDR Input Hold	0.8	-	1.0	-	ns
tDQSQ	DQSM-DQ Skew	-	0.75	-	0.8	ns
tQHS	Data Hold Skew factor	-	0.90	-	0.95	ns
tQH	DQ hold time from DQSM	tHP-tQHS	-	tHP-tQHS	-	ns
tLZ	Clock to DQ Low-Z	0	-	0	-	ns
tHZ	CS# Inactive to DQSM and DQ High-Z	-	7	-	7	ns
tCSM	Chip Select Maximum Low Time	~ 85°C	4	-	4	us
		85+°C ~ 125°C	1	-	1	us

8.2.3 WRITE Timing Parameters (1.8V)

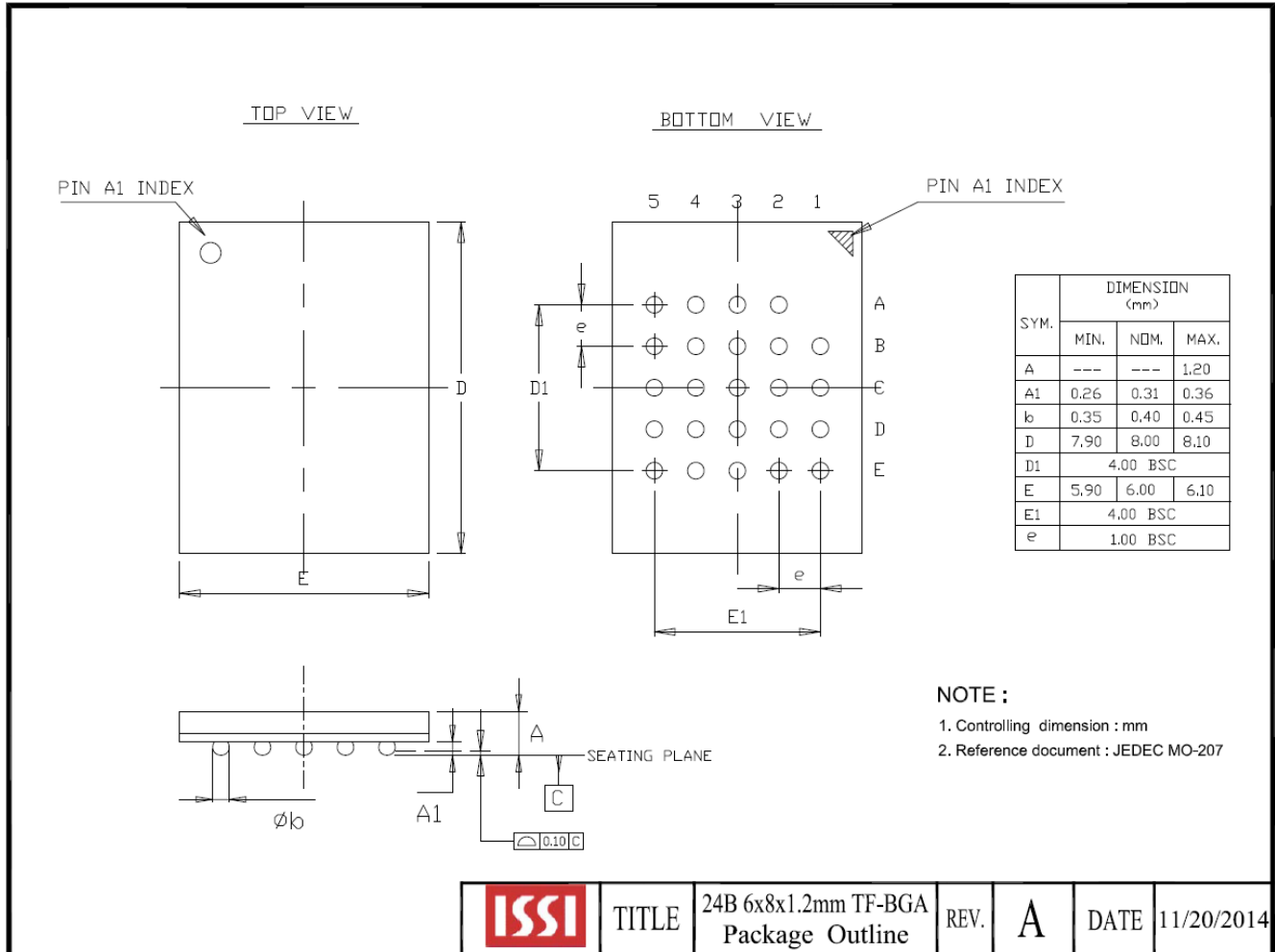
Symbol	Parameter	200MHz		166MHz		Unit
		Min.	Max.	Min.	Max.	
tRWR	Read-Write Recovery Time	45	-	54	-	ns
tCK	Clock(CLK) Period	5	-	6	-	ns
tCH	Clock High level width	0.45	-	0.45	-	tCKmin
tCL	Clock Low level width	0.45	-	0.45	-	tCKmin
tHP	Clock half period	Min(tCH,tCL)	-	Min(tCH,tCL)	-	ns
tDQSV	CS# Active to DQSM valid	-	12	-	12	ns
tCSP	CS# High Between READ/WRITE	6	-	6	-	ns
tCSS	CS# Setup to next CLK Rising Edge	3	-	3	-	ns
tCSH	CS# Hold After CLK Falling Edge	2	-	2	-	ns
tSS	SDR Input Setup	0.6	-	0.9	-	ns
tSH	SDR Input Hold	0.6	-	0.9	-	ns
tDS	DDR Input Setup	0.4	-	0.6	-	ns
tDH	DDR Input Hold	0.4	-	0.6	-	ns
tDMV	Data Mask Valid (DQSM setup to end of initial latency)	0	-	0	-	ns
tCSM	Chip Select Maximum	~ 85°C	4	-	4	us
	Low Time	85+°C ~ 125°C	1	-	1	us

8.2.4 WRITE Timing Parameters (3.0V)

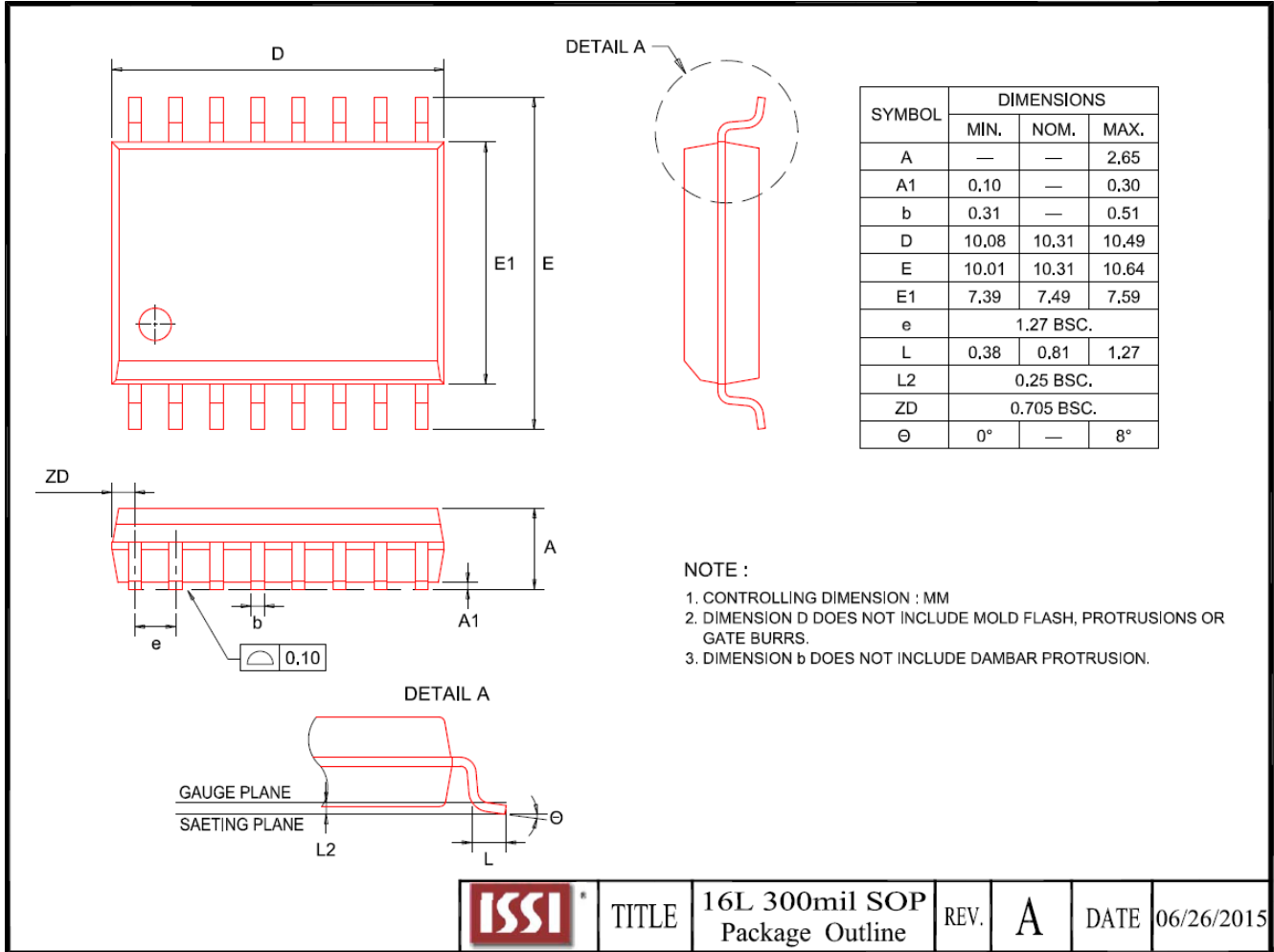
Symbol	Parameter	133Mhz		100Mhz		Unit	
		Min.	Max.	Min.	Max.		
tRWR	Read-Write Recovery Time	45	-	50	-	ns	
tCK	Clock(CLK) Period	7.5	-	10	-	ns	
tCH	Clock High level width	0.45	-	0.45	-	tCKmin	
tCL	Clock Low level width	0.45	-	0.45	-	tCKmin	
tHP	Clock half period	Min(tCH,tCL)	-	Min(tCH,tCL)	-	ns	
tDQSV	CS# Active to DQSM valid	-	12	-	12	ns	
tCSP	CS# High Between READ/WRITE	7.5	-	10	-	ns	
tCSS	CS# Setup to next CLK Rising Edge	3	-	3	-	ns	
tCSH	CS# Hold After CLK Falling Edge	2	-	2	-	ns	
tSS	SDR Input Setup	1.2	-	1.5	-	ns	
tSH	SDR Input Hold	1.2	-	1.5	-	ns	
tDS	DDR Input Setup	0.8	-	1.0	-	ns	
tDH	DDR Input Hold	0.8	-	1.0	-	ns	
tDMV	Data Mask Valid (DQSM setup to end of initial latency)	0	-	0	-	ns	
tCSM	Chip Select Maximum Low Time	~ 85°C	-	2	-	2	uS
		85+°C ~ 125°C	-	1	-	1	us

8. PACKAGE TYPE INFORMATION

8.1 24-BALL THIN PROFILE FINE PITCH BGA 6X8MM 5X5 BALL ARRAY (B)

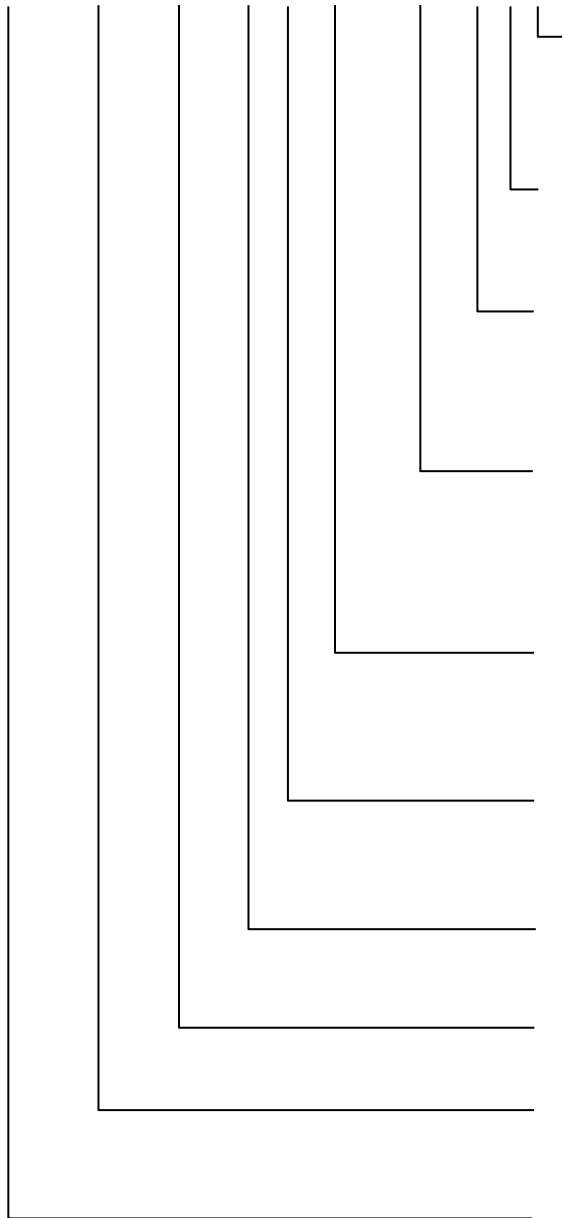


8.2 16-LEAD PLASTIC SMALL OUTLINE PACKAGE (300 MILS BODY WIDTH) (M)



9. ORDERING INFORMATION – Valid Part Numbers

IS66 WVQ 4M4 _ D ALL - 200 B L I



TEMPERATURE RANGE

- I = Extended (-40°C to +85°C)
- E = Extended (-40°C to +105°C)
- A3 = Automotive Grade (-40°C to +125°C)

PACKAGING CONTENT

- L = RoHS compliant

PACKAGE Type ⁽¹⁾

- B = 24-ball TFBGA 6x8mm 5x5 ball array
- M = 16-pin SOIC 300mil
- W = KGD (Call Factory)

Frequency

- 200 = 200MHz
- 166 = 166MHz
- 133 = 133MHz
- 100 = 100MHz

VDD

- ALL = 1.8V
- BLL = 3.0V

Die Revision

- D = die rev D

On Chip ECC

- BLANK = No On Chip ECC

Density/Org.

- 4M4 = 4Mbx4=16Mb

PSRAM Product Type.

- WVQ = QuadRAM

BASE PART NUMBER

- IS = Integrated Silicon Solution Inc.
- 66 = PSRAM
- 67 = PSRAM for Automotive



Industrial Temperature Range (-40°C to +85°C)

Config.	Voltage	Package	Frequency (MHz)	Order Part Number
4Mbx4	1.8V	24-ball TFBGA 6x8mm 5x5 ball array	200	IS66WVQ4M4DALL-200BLI
			166	IS66WVQ4M4DALL-166BLI
		16-pin SOIC 300mil	133	IS66WVQ4M4DALL-133MLI
			100	IS66WVQ4M4DALL-100MLI
	3.0V	24-ball TFBGA 6x8mm 5x5 ball array	133	IS66WVQ4M4DBLL-133BLI
			100	IS66WVQ4M4DBLL-100BLI
		16-pin SOIC 300mil	133	IS66WVQ4M4DBLL-133MLI
			100	IS66WVQ4M4DBLL-100MLI

Extended Temperature Range (-40°C to +105°C)

Config.	Voltage	Package	Frequency (MHz)	Order Part Number
4Mbx4	1.8V	24-ball TFBGA 6x8mm 5x5 ball array	200	IS66WVQ4M4DALL-200BLE
			166	IS66WVQ4M4DALL-166BLE
		16-pin SOIC 300mil	133	IS66WVQ4M4DALL-133MLE
			100	IS66WVQ4M4DALL-100MLE
	3.0V	24-ball TFBGA 6x8mm 5x5 ball array	133	IS66WVQ4M4DBLL-133BLE
			100	IS66WVQ4M4DBLL-100BLE
		16-pin SOIC 300mil	133	IS66WVQ4M4DBLL-133MLE
			100	IS66WVQ4M4DBLL-100MLE

Automotive A3 Temperature Range (-40°C to +125°C)

Config.	Voltage	Package	Frequency (MHz)	Order Part Number
4Mbx4	1.8V	24-ball TFBGA 6x8mm 5x5 ball array	166	IS67WVQ4M4DALL-166BLA3
			133	IS67WVQ4M4DALL-133MLA3
		16-pin SOIC 300mil	100	IS67WVQ4M4DALL-100MLA3
	3.0V	24-ball TFBGA 6x8mm 5x5 ball array	133	IS67WVQ4M4DBLL-133BLA3
			100	IS67WVQ4M4DBLL-100BLA3
		16-pin SOIC 300mil	133	IS67WVQ4M4DBLL-133MLA3
			100	IS67WVQ4M4DBLL-100MLA3